AMENDMENTS TO THE CLAIMS

Claims 1-169 (Canceled)

- 170. (currently amended) A semiconductor component comprising:
- a thinned semiconductor die having an outline, a circuit side, a <u>planarized</u> back side, four peripheral edges, and a plurality of die contacts on the circuit side;
 - a plurality of contact bumps on the die contacts;
- a <u>planarized</u> first polymer layer covering the circuit side, the contact bumps and the peripheral edges, the first polymer layer having edge polymer layers of a selected thickness on covering and rigidifying the peripheral edges;
- a <u>planarized</u> second polymer layer covering the back side, the first polymer layer and the second polymer layer encapsulating the die on six sides such that the component has a chip scale outline corresponding to the outline of the die plus the selected thickness of the edge polymer layers; and
 - a plurality of terminal contacts on the contact bumps.
- 171. (currently amended) The semiconductor component of claim 170 wherein the die comprises a tested and burned in die and the component comprises a known good component (KGC).
- is initially contained on a semiconductor wafer and is tested and burned in on the wafer.
- 172. (previously presented) The semiconductor component of claim 170 wherein the contact bumps comprise metal bumps in a dense area array.

- 173. (previously presented) The semiconductor component of claim 170 wherein the terminal contacts comprise conductive bumps or balls in a grid array.
- 174. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer and the contact bumps have a same planar surface.
- 175. (currently amended) The semiconductor component of claim 170 wherein the second polymer layer covers planarized edges of the edge polymer layers.

 layer has a second planar surface.
- 176. (previously presented) The semiconductor component of claim 170 further comprising a plurality of conductive vias in the thinned die in electrical communication with the die contacts and with the terminal contacts.
- 177. (previously presented) The semiconductor component of claim 176 further comprising a plurality of second die contacts on the second polymer layer in electrical communication with the conductive vias.
- 178. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a photopolymer.
- 179. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a wafer level underfill.

Claims 180-261 (canceled)

262. (currently amended) The semiconductor component of claim 170 wherein the <u>contact bumps comprise planarized</u> surfaces.

backside comprises a planar surface.

- 263. (previously presented) The semiconductor component of claim 170 wherein the backside comprises a polished surface.
- 264. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a tape material.
- 265. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer on each edge comprises a portion of a polymer filled trench.
- 266. (currently amended) The semiconductor component of claim 170 wherein the edge polymer layers and the back side have a same planar surface.

 second polymer layer includes at least one pin one
- 267. (currently amended) The semiconductor component of claim 170 wherein the edge polymer layers have a selected thickness which is different than a thickness of the first polymer layer.

first polymer layer includes at least one pin one indicator.

- 268. (previously presented) The semiconductor component of claim 170 wherein the thinned die comprises a tested and burned in die.
- 269. (previously presented) The semiconductor component of claim 170 wherein the thinned die is contained

indicator.

on a semiconductor wafer having a polymer support dam proximate to edges thereof.

- 270. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer comprises a first polymer material and the second polymer layer comprises a second polymer material.
- 271. (previously presented) The semiconductor component of claim 170 wherein the first polymer layer comprises parylene.
- 272. (withdrawn) The semiconductor component of claim 170 wherein the edge polymer layers form a recess and the second polymer layer is within the recess.